



BLY92C

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **BLY92C** is Designed for Class C FM Amplifier Applications up to 250 MHz.

FEATURES:

- $P_G = 11$ dB Typical at 175 MHz
- High Load VSWR Capability
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB}	65 V
V_{CE}	35 V
V_{EB}	4.0 V
P_{DISS}	40 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$4.4^\circ C/W$

PACKAGE STYLE .380" 4L STUD

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B	.980/24.89	
C	.370/9.40	.385/9.78
D	.004/0.10	.007/0.18
E	.320/8.13	.330/8.38
F	.100/2.54	.130/3.30
G	.450/11.43	.490/12.45
H	.090/2.29	.100/2.54
I	.155/3.94	.175/4.45
J		.750/19.05

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

ORDER CODE: ASI10758

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	35			---
C_{ob}	$V_{CB} = 30$ V $f = 1.0$ MHz		40	50	pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 15$ W $f = 175$ MHz	10	11		dB
η_c		50	60		%